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RoHS 2002/95/EC

NTE2676
Silicon NPN Transistor
High Voltage, High Speed Switch
TO3P(H)IS Type Package

Features:
- High Breakdown Voltage: V_{CBO} = 1500V Min
- High Switching Speed
- Low Saturation Voltage

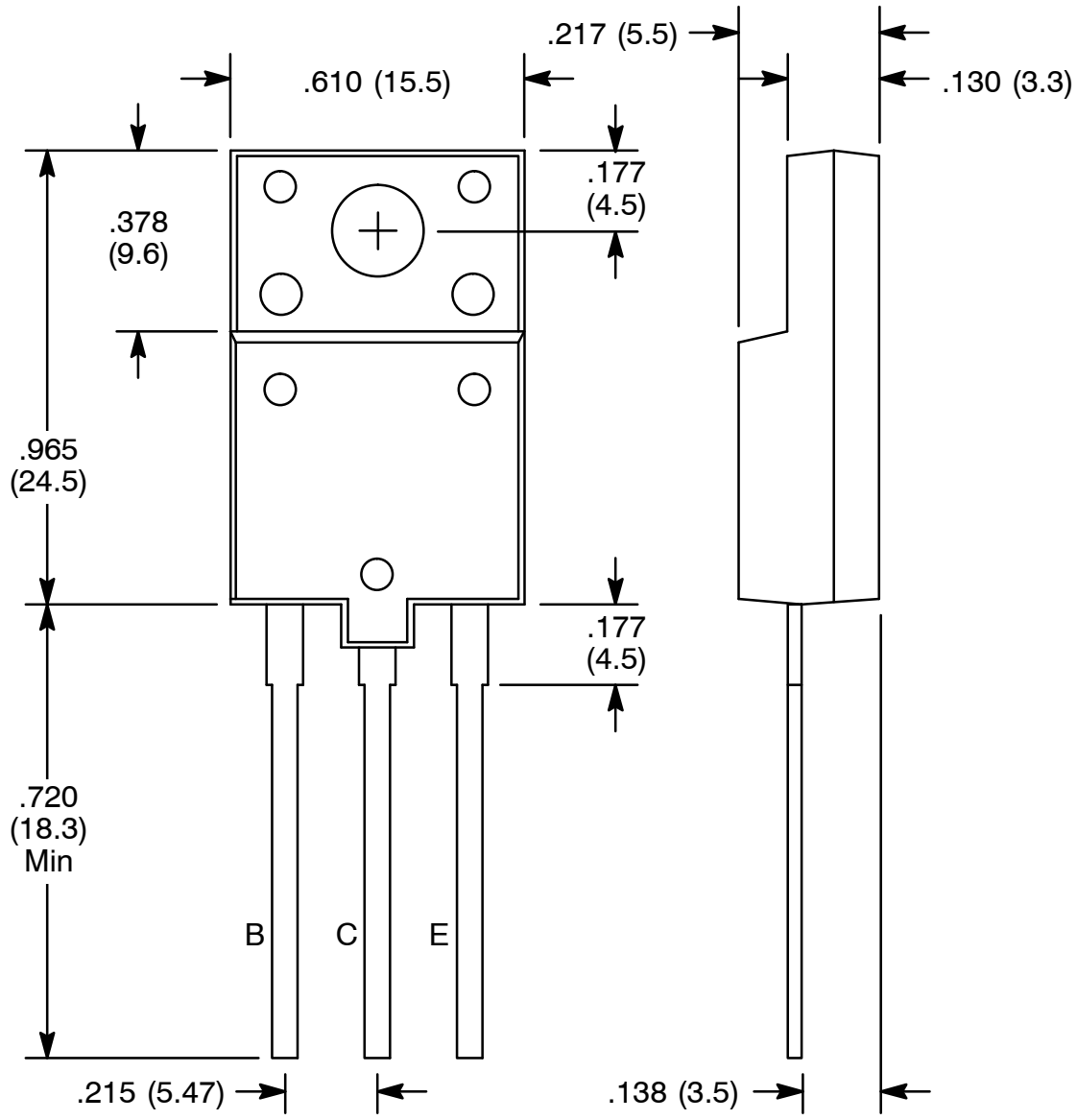
Applications:
- Color TV Horizontal Deflection Output

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 1500V
Collector–Emitter Voltage, V_{CEO} 600V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
  Continuous 10A
  Pulse 20A
Continuous Base Current, I_B 5A
Collector Power Dissipation (T_C = +25°C), P_C 50W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_C = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 6A, I_B = 1.5A	–	–	3.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 6A, I_B = 1.5A	–	–	1.4	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 1500V, I_E = 0	–	–	1.0	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	10	A
DC Current Gain	h_{FE}	I_C = 1A, V_{CE} = 5V	10	–	30	
		I_C = 6A, V_{CE} = 5V	4	–	8	
Current Gain Bandwidth Product	f_T	I_C = 100mA, V_{CE} = 10V	–	1.7	–	MHz
Output Capacitance	C_{OB}	I_E = 0, V_{CB} = 10V, f_{test} = 1.0MHz	–	135	–	pF
Storage Time	t_{stg}	I_{CP} = 6A, $I_{B1(end)}$ = 1.5A, f_H = 15.75kHz	–	–	11	s
Fall Time	t_f		–	–	0.7	s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